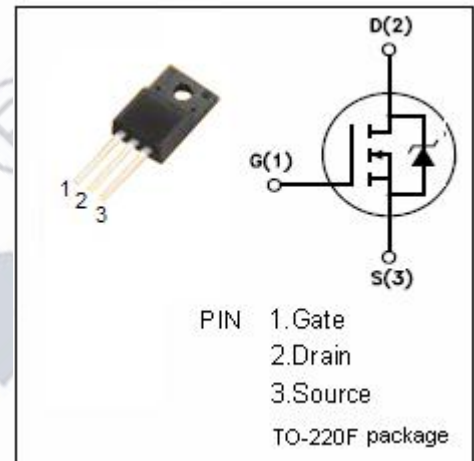


isc N-Channel Mosfet Transistor**HG2N60****• FEATURES**

- Drain Current $-I_D = 2A @ T_C = 25^\circ C$
- Drain Source Voltage-
: $V_{DSS} = 600V(\text{Min})$
- Static Drain-Source On-Resistance
: $R_{DS(on)} = 4.5 \Omega (\text{Max})$
- Avalanche Energy Specified
- Fast Switching
- Simple Drive Requirements

• DESCRIPTION

- High efficiency switch mode power supply.
Charger
UPS power supply.

**• ABSOLUTE MAXIMUM RATINGS($T_a = 25^\circ C$)**

SYMBOL	PARAMETER	VALUE	UNIT
V_{DSS}	Drain-Source Voltage	600	V
V_{GS}	Gate-Source Voltage-Continuous	± 30	V
I_D	Drain Current-Continuous	2	A
I_{DM}	Drain Current-Single Pulsed	6	A
P_D	Total Dissipation @ $T_C = 25^\circ C$	50	W
T_j	Max. Operating Junction Temperature	150	$^\circ C$
T_{stg}	Storage Temperature	-55~150	$^\circ C$

isc N-Channel Mosfet Transistor**HG2N60****ELECTRICAL CHARACTERISTICS** $T_c=25^{\circ}\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	$V_{GS}=0$; $I_D=0.25\text{mA}$	600		V
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}$; $I_D=0.25\text{mA}$	2	4	V
$R_{DS(on)}$	Drain-Source On-Resistance	$V_{GS}=10\text{V}$; $I_D=1\text{A}$		4.5	Ω
I_{GSS}	Gate-Body Leakage Current	$V_{GS}=\pm 30\text{V}$; $V_{DS}=0$		± 100	nA
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS}=600\text{V}$; $V_{GS}=0$		5	μA
V_{SD}	Forward On-Voltage	$I_S=2\text{A}$; $V_{GS}=0$		1.4	V